

Title (en)
ELECTRICAL BONDING OF A SEMICONDUCTOR JUNCTION

Title (de)
KONTAKTIERUNG EINER HALBLEITERZONE

Title (fr)
METALLISATION D'UNE JONCTION SEMI-CONDUCTRICE

Publication
EP 0996977 A1 20000503 (DE)

Application
EP 98944992 A 19980715

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Abstract (en)
[origin: WO9904427A1] The invention concerns a method for the electrical bonding of semiconductor components, and a corresponding semiconductor component obtained by said method. A method is disclosed for bonding a buried semiconductor coat (1), via a feedthrough (4) Said method consists in producing the feedthrough (4) in an insulating layer (2) for the electrical bonding of at least one buried semiconductor coat (1), and is characterised in that it comprises steps consisting in: producing a highly doped polysilicon layer (7) on the insulating layer surface (2), the feedthrough (4) being filled at least partially with highly doped polysilicon, and in applying a metal coating (3) on said highly doped polysilicon layer (7) to produce ohmic contact outwards.

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